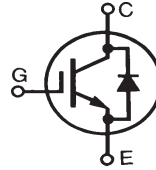


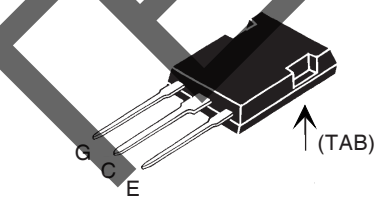
# High Voltage IGBT with Diode

## IXGX 32N170H1

$$\begin{aligned}
 V_{CES} &= 1700 \text{ V} \\
 I_{C25} &= 75 \text{ A} \\
 V_{CE(sat)} &= 3.3 \text{ V} \\
 t_{fi(typ)} &= 290 \text{ ns}
 \end{aligned}$$



PLUS247 (IXGX)



G = Gate,  
E = Emitter,  
C = Collector,  
TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1700	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	75	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	32	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	200	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 5\Omega$ Clamped inductive load	$I_{CM} = 90$ @ $0.8 V_{CES}$	A
$t_{SC}$	$T_J = 125^\circ\text{C}, V_{CE} = 1200 \text{ V}; V_{GE} = 15 \text{ V}, R_G = 10\Omega$	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	350	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$F_C$	Mounting force with chip	22...130/5...30	N/lb
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
<b>Weight</b>		6	g

### Features

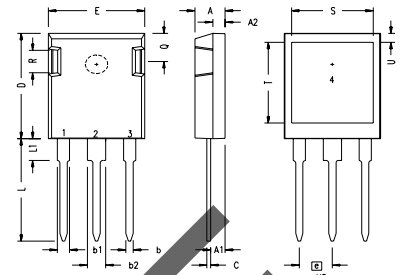
- High current handling capability
- MOS Gate turn-on  
- drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

### Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$	1700		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			500 $\mu\text{A}$ 8 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$			2.5 V 3.0 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$I_C = I_{C25}; V_{CE} = 10\text{ V}$ Note 2	25	33	S
$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		3500	pF
$C_{oes}$			250	pF
$C_{res}$			40	pF
$Q_g$	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		155	nC
$Q_{ge}$			30	nC
$Q_{gc}$			51	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $R_G = 2.7\ \Omega, V_{CE} = 0.8 V_{CES}$ Note 3		45	ns
$t_{ri}$			38	ns
$t_{d(off)}$			270	500 ns
$t_{fi}$			250	500 ns
$E_{off}$			15	25 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $R_G = 2.7\ \Omega, V_{CE} = 0.8 V_{CES}$ Note 3		48	ns
$t_{ri}$			42	ns
$E_{on}$			6.0	mJ
$t_{d(off)}$			360	ns
$t_{fi}$			560	ns
$E_{off}$		22	mJ	
$R_{thJC}$				0.35 K/W
$R_{thCK}$		0.15		K/W

**PLUS247 Outline (IXGX)**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
O	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 70\text{ A}, V_{GE} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			2.7 V
$I_{RM}$	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}, -di_F/dt = 800\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}$		50	A
$t_{rr}$			150	ns
$R_{thJC}$				0.4 K/W

- Notes:
- Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.
  - Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$
  - Switching times may increase for  $V_{CE}$  (Clamp)  $> 0.8 \cdot V_{CES}$ , higher  $T_J$  or increased  $R_G$ .
  - See DH60-18A and IXGH32N170A datasheets for additional characteristics

IXYS reserves the right to change limits, test conditions, and dimensions.